



Si4835BDY vs. Si4835DY

Description: P-Channel, 30 V (D-S) MOSFET

Package: SOIC-8

Pin Out: Identical

Part Number Replacements:

- Si4835BDY Replaces Si4835DY
- Si4835BDY-E3 (Lead (Pb)-free version) Replaces Si4835DY
- Si4835BDY-T1 Replaces Si4835DY-T1
- Si4835BDY-T1-E3 (Lead (Pb)-free version) Replaces Si4835DY-T1

ABSOLUTE MAXIMUM RATINGS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted				
Parameter	Symbol	Si4835BDY	Si4835DY	Unit
Drain-Source Voltage	V_{DS}	- 30	- 30	V
Gate-Source Voltage	V_{GS}	± 25	± 25	
Continuous Drain Current	$T_A = 25\text{ }^\circ\text{C}$	- 9.6	- 8.0	A
	$T_A = 70\text{ }^\circ\text{C}$	- 7.7	- 6.4	
Pulsed Drain Current	I_{DM}	- 50	- 50	
Continuous Source Current (MOSFET Diode Conduction)	I_S	- 2.1	- 2.3	
Power Dissipation	$T_A = 25\text{ }^\circ\text{C}$	2.5	2.5	W
	$T_A = 70\text{ }^\circ\text{C}$	1.6	1.6	
Operating Junction and Storage Temperature Range	T_j and T_{stg}	- 55 to 150	- 55 to 150	$^\circ\text{C}$
Maximum Junction-to-Ambient	R_{thJA}	50	50	$^\circ\text{C/W}$

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted								
Parameter	Symbol	Si4835BDY			Si4835DY			Unit
		Min	Typ	Max	Min	Typ	Max	
Static								
Gate-Threshold Voltage	$V_{G(th)}$	- 1.0		- 3.0	- 1.0			V
Gate-Body Leakage	I_{GSS}			± 100			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}			- 1			- 1	μA
On-State Drain Current	$V_{GS} = - 10\text{ V}$	- 50			- 40			A
	$V_{GS} = - 4.5\text{ V}$	NS			- 10			
Drain-Source On-Resistance	$V_{GS} = - 10\text{ V}$		0.014	0.018		0.0155	0.019	Ω
	$V_{GS} = - 4.5\text{ V}$		0.023	0.030		0.027	0.033	
Forward Transconductance	g_{fs}		30			17		S
Diode Forward Voltage	V_{SD}		- 0.8	- 1.2		- 0.75	- 1.2	V
Dynamic								
Total Gate Charge	Q_g		25	37		21	31	nC
Gate-Source Charge	Q_{gs}		6.5			6.5		
Gate-Drain Charge	Q_{gd}		12.5			8		
Gate Resistance	R_g	1.0	2.9	4.9	1.0	2.6	4.4	Ω
Switching								
Turn-On Time	$t_{d(on)}$		15	25		16	30	ns
	t_r		13	20		13	25	
Turn-Off Time	$t_{d(off)}$		60	100		56	100	
	t_f		45	70		30	60	
Source-Drain Reverse Recovery Time	t_{rr}		45	80		40	80	

NS denotes parameter not specified.

Specification comparisons are supplied as a courtesy to compare two devices and do not constitute a commercial product datasheet or any guarantee of identical performance. Designers should refer to the appropriate datasheets of the same number for guaranteed specification limits.